

# Density Functional Theory: Part 2. Practical concepts & Basic Tutorials with Quantum Espresso

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UANTUMESPRESSO

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## Input file: Advanced topics

- 1. Metals and fractional occupations
- 2. Structural optimization
- 3. Low-dimensional systems
- Spin polarization & magnetism (not examined here)

```
&CONTROL
 calculation = "relax",
 etot conv thr = 1.0D-4
 forc conv thr = 1.0D-3
 prefix
         = "CO".
 pseudo dir = "./",
&SYSTEM
 ibrav = 0
 nat = 2, ntyp = 2,
 nbnd = 6.
 ecutwfc = 50.
nspin = 2.
 starting_magnetization(1)=0.1
 occupations ='smearing'
 degauss =0.001,
&ELECTRONS
&IONS
CELL PARAMETERS {bohr}
30.0 0.0 0.0
 0.0 12.0 0.0
      0.0 12.0
 0.0
ATOMIC SPECIES
O 1.00 O.pw-mt fhi.UPF
C 1.00 C.pw-mt fhi.UPF
ATOMIC_POSITIONS {bohr}
C 5.0 0.0 0.0 100
K POINTS (Gamma)
```

### 1. Metals and fractional occupations

Recall:

$$\langle P \rangle = \frac{\Omega}{(2\pi)^3} \sum_{n \, occ_{BZ}} \int_{R} P_n(\mathbf{k}) d^3 k$$

- For metals, at T=0, this corresponds to (for highest band) an integral over all wave-vectors contained within the Fermi surface, i.e., for highest band, sharp discontinuity in k-space between occupied and unoccupied states...need many k-points to reproduce this accurately.
- Also can lead to scf convergence problems because of band-crossings above/below Fermi level.
- Solve by "smearing".



#### Smearing in Quantum-ESPRESSO

occupations 'smearing'

Instruction: use smearing

Type of smearing

degauss

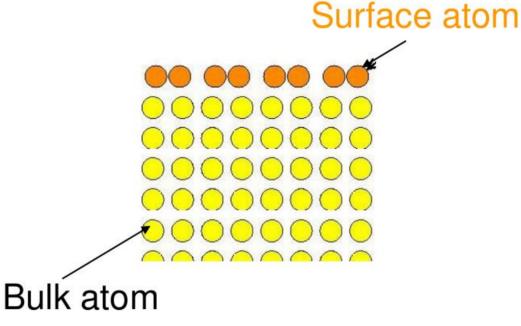
Smearing width

In Ry typical 0.01

Methfessel & Paxton, Phys. Rev. B 40, 3616 (1989). Marzari & Vanderbilt, Phys Rev. Lett. 82, 3296 (1999).

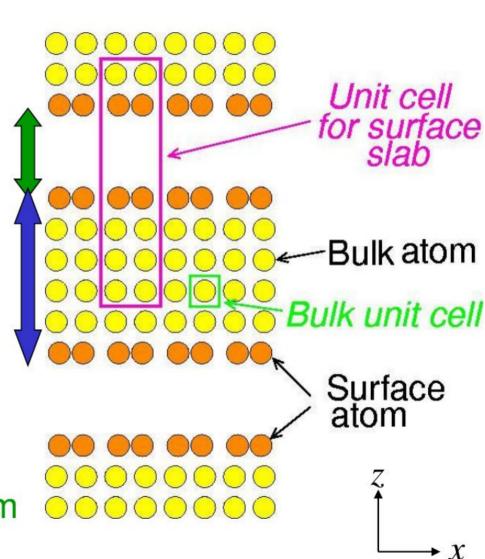
 Example 1: Want to study properties of a system with a surface.

 Presence of surface ⇒ No periodicity along z.

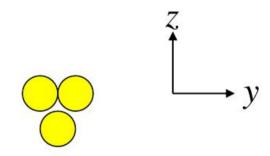




- Example 1: Want to study properties of a system with a surface.
- Presence of surface ⇒ No periodicity along z.
- Use a supercell: artificial periodicity along z by repeating slabs separated by vacuum.
- Have to check convergence w.r.t. slab thickness & vacuum thickness.

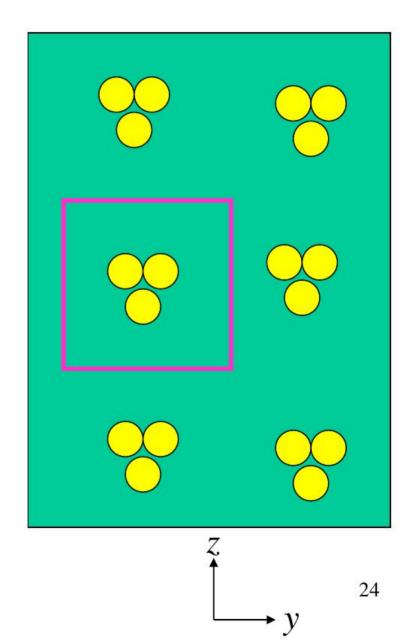


 Example 2: Want to study properties of a nanowire.

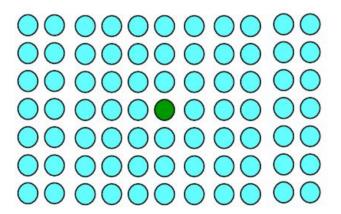


Example 3: Want to study properties of a cluster

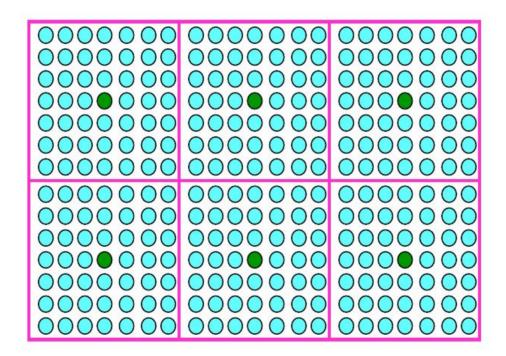
- Example 2: Want to study properties of a nanowire ⇒ introduce artificial periodicity along y & z.
- Example 3: Want to study properties of a cluster ⇒ introduce artificial periodicity along x, y & z.



 Example 4: Want to study a system with a defect, e.g., a vacancy or impurity:



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#### Artificially Periodic Systems ⇒ Large Unit Cells

 Note: In all these cases, to minimize the effects of the artificially introduced periodicity, need a large unit cell.



Long a<sub>1</sub>, a<sub>2</sub>, a<sub>3</sub> (primitive lattice vectors)

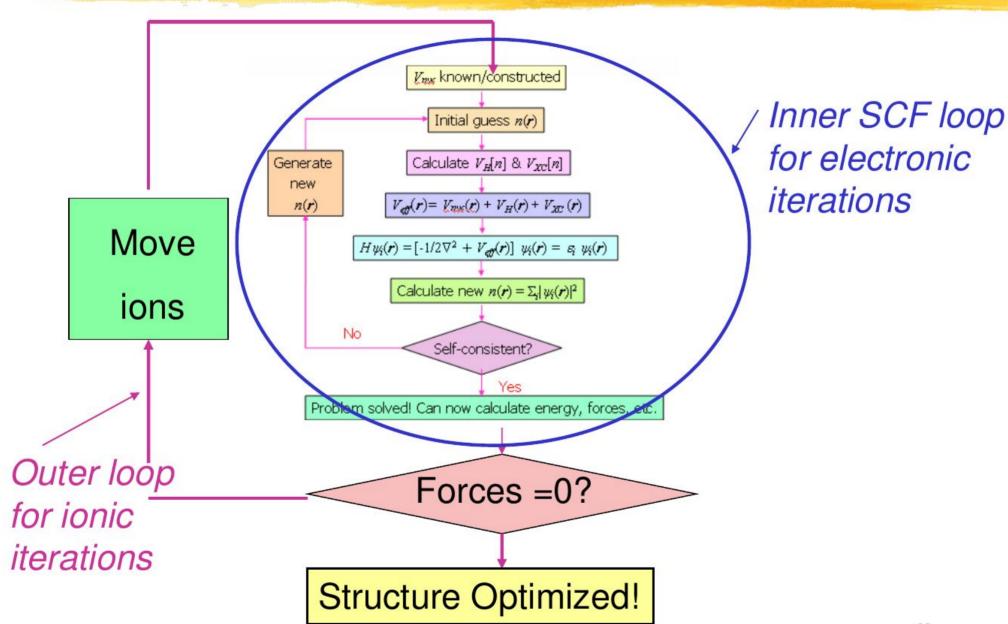


• Short  $\mathbf{b}_1$ ,  $\mathbf{b}_2$ ,  $\mathbf{b}_3$  (primitive reciprocal lattice vectors)

• Many G's will fall within  $E_{cut}$  sphere!

- => Many G-vectors (for the same cutoff)
- => Fewer k-points (2D grid, 1D grid, or Gamma point only)

#### 3 An Outer Loop: Ionic Relaxation



#### **Forces**

- Need for geometry optimization and molecular dynamics.
- Could get as finite differences of total energy too expensive!
- Use force (Hellmann-Feynman) theorem:
  - Want to calculate the force on ion *I*:

$$\mathbf{F}_I = -rac{d}{d\mathbf{R}_I} \langle \Psi | H | \Psi 
angle$$

- Get three terms:

$$\mathbf{F}_{I} = -\langle \Psi | \frac{\partial H}{\partial \mathbf{R}_{I}} | \Psi \rangle - \langle \frac{\partial \Psi}{\partial \mathbf{R}_{I}} | H | \Psi \rangle - \langle \Psi | H | \frac{\partial \Psi}{\partial \mathbf{R}_{I}} \rangle$$

When  $|\Psi\rangle$  is an eigenstate,  $H|\Psi\rangle=E|\Psi\rangle$ 

-Substitute this...

#### Forces (contd.)

The force is now given by

$$\mathbf{F}_{I} = -\langle \Psi | \frac{\partial H}{\partial \mathbf{R}_{I}} | \Psi \rangle - E \langle \frac{\partial \Psi}{\partial \mathbf{R}_{I}} | \Psi \rangle - E \langle \Psi | \frac{\partial \Psi}{\partial \mathbf{R}_{I}} \rangle$$
$$= -\langle \Psi | \frac{\partial H}{\partial \mathbf{R}_{I}} | \Psi \rangle - E \frac{\partial}{\partial \mathbf{R}_{I}} \langle \Psi | \Psi \rangle$$

- Note that we can now calculate the force from a calculation at ONE configuration alone – huge savings in time.
- If the basis depends upon ionic positions (not true for plane waves), would have extra terms = Pulay forces.
- $|\Psi\rangle$  should be exact eigenstate, i.e., scf well-converged!

Input parameter tprnfor

#### Geometry Optimization With Forces

 Especially useful for optimizing internal degrees of freedom, surface relaxation, etc.

```
calculation = 'relax'
```

Choice of algorithms for ionic relaxation, e.g., steepest descent, BFGS.

NAMELIST & IONS

Input parameter ion\_dynamics